



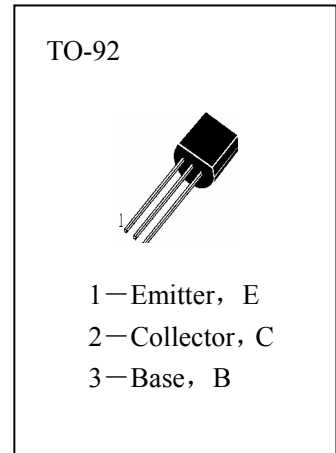
H1268

■ LOW NOISE AMPLIFIER APPLICATION.

HIGH VOLTAGE APPLICATION

■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

- T_{stg}——Storage Temperature..... -55~150°C
- T_j——Junction Temperature.....150°C
- P_C——Collector Dissipation.....300mW
- V_{CB0}——Collector-Base Voltage.....-120V
- V_{CEO}——Collector-Emitter Voltage.....-120V
- V_{EBO}——Emitter-Base Voltage.....-5V
- I_C——Collector Current.....-100mA



■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CEO}	Collector-Emitter Breakdown Voltage	-120			V	I _C =-1mA, I _B =0
I _{CBO}	Collector Cut-off Current			-100	nA	V _{CB} =-120V, I _E =0
I _{EBO}	Emitter Cut-off Current			-100	nA	V _{EB} =-5V, I _C =0
H _{FE}	DC Current Gain	200		700		V _{CE} =-6V, I _C =-2mA
V _{CE(sat)}	Collector- Emitter Saturation Voltage			-0.3	V	I _C =-10mA, I _B =-1mA
V _{BE}	Base-Emitter Voltage		-0.65		V	I _C =-6A, I _B =-2mA
f _T	Current Gain-Bandwidth Product		100		MHz	V _{CE} =-6V, I _C =-1mA
C _{ob}	Output Capacitance		4.0		pF	V _{CB} =-10V, I _E =0, f=1MHz
NF	Noise Figure			6		V _{CE} =-6V, I _C =-100 μ A, f=10Hz, R _g =10K Ω
				2	dB	V _{CE} =-6V, I _C =-100 μ A, f=1Hz, R _g =10K Ω
			3			V _{CE} =-6V, I _C =-100 μ A, f=1Hz, R _g =100K Ω

■ h_{FE} Classification

GR

BL

200—400

350—700